TO-252 ḾḾḪ ₰ ᵍ⁀ ‖ ᒣ

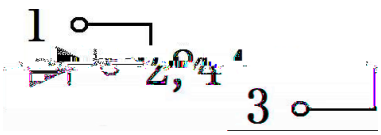
Schottky Barrier Diode in a TO-252 Plastic Package.

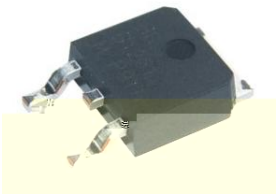
ᵪ* ᵇ ⁼ ⊥ ǐ ᵀ ı ʌ Ḥ* ᵇ ᵶ ᑌ V_F(typ)=0.2V ı Ч â ᵪ □ Ч ḧ ớ

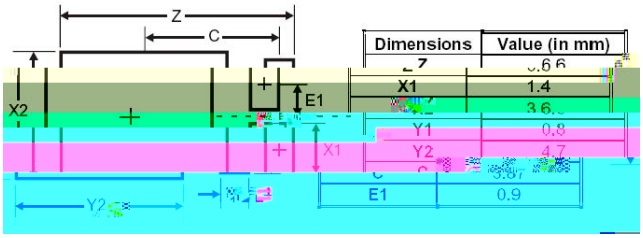
High Forward Surge Capability, Ultra Low Forward Voltage Drop V_F(typ)=0.2V, Excellent High Temperature Stability.

ᵮ ᵪ ḽ Ḥ ᵶ ᶻ ↄ ⊥ Ꝙ ⊥ ‖ ᒣ ı ʌ ⊥ ‖ ᒣ ı Ȝ ǐ ‖ ᒣ

For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications.







PIN1 χ Anode PIN 2,4 χ Cathode PIN 3 χ Anode Suggested Pad layout

ð ᴍ ᵑ ب ″ See Marking Instructions.

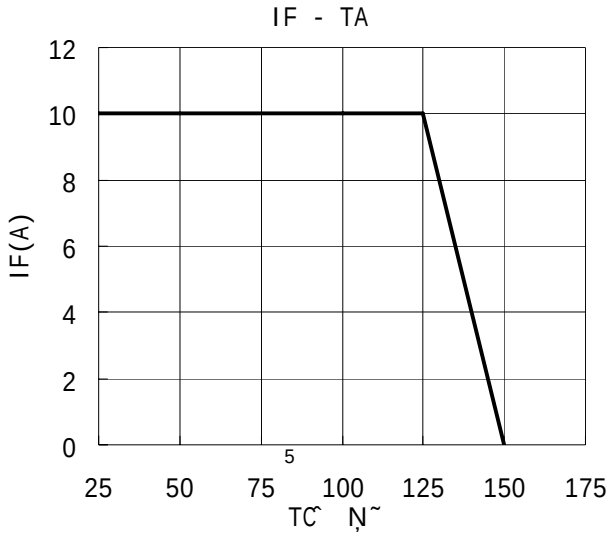
v ¨Ω Parameter	ч N Symbol	¨Ω Ö Rating	D Ц Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage Peak Reverse Voltage	V_{RRM} V_{RWM} V_{RM}	45	V
RMS Reverse voltage	$V_{R(RMS)}$	31.5	V
Average Rectified Output Current	I_O	10	A
Non-Repetitive Peak Forward Surge Current	I_{FSM}	250	A
Junction Temperature Range	$T_{j\ MAX}$	150	
Storage Temperature Range	T_{stg}	-55˙ 150	
Typical Thermal Resistance	$R_{\theta JA}$˝ Note 1˝	73	/W

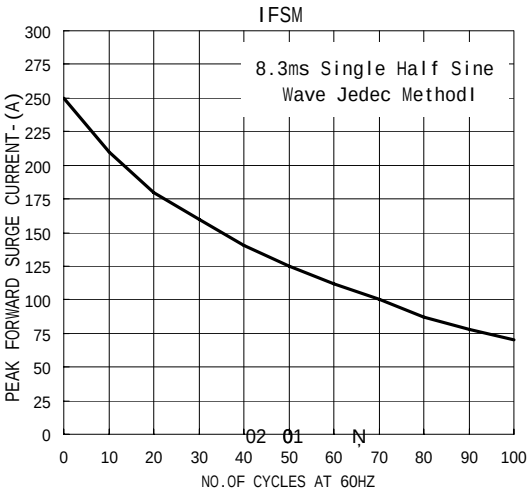
v ¨Ω Parameter	ч N Symbol	╨ :┆ Ţ Test Conditions	ѡ ņ Ö Min	Ɛ ʒ Ö Typ	ѡ ᶻ Ö Max	D Ц Unit
Reverse Voltage	V_R	I_R=0.5mA	45			V
Forward voltage	V_F	I_F=2A T_J=25		0.33	0.38	V
		I_F=2A T_J=125		0.20		V
		I_F=10A T_J=25		0.42	0.46	V
		I_F=10A T_J=125		0.35		V
Instantaneous Reverse Current	I_R˝ Note 2˝	V_R=45V T_J=25		0.06	0.12	mA
		V_R=45V T_J=100			12	mA
		V_R=45V T_J=125			50	mA

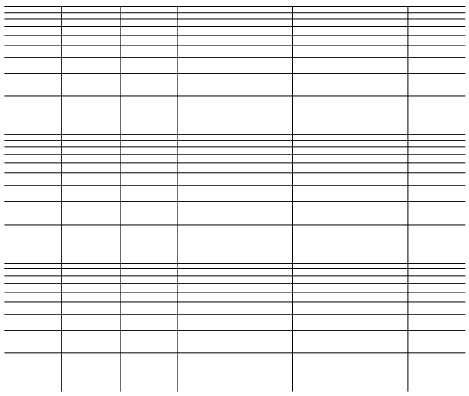
├2Notes'

4⁞ IU07 SFE ı 5 ´ и ڤ ı ѡ Ң ấ ɲ ` ų ṕ /FR-4 PCB, 2oz. Copper, minimum recommended pad layout per.

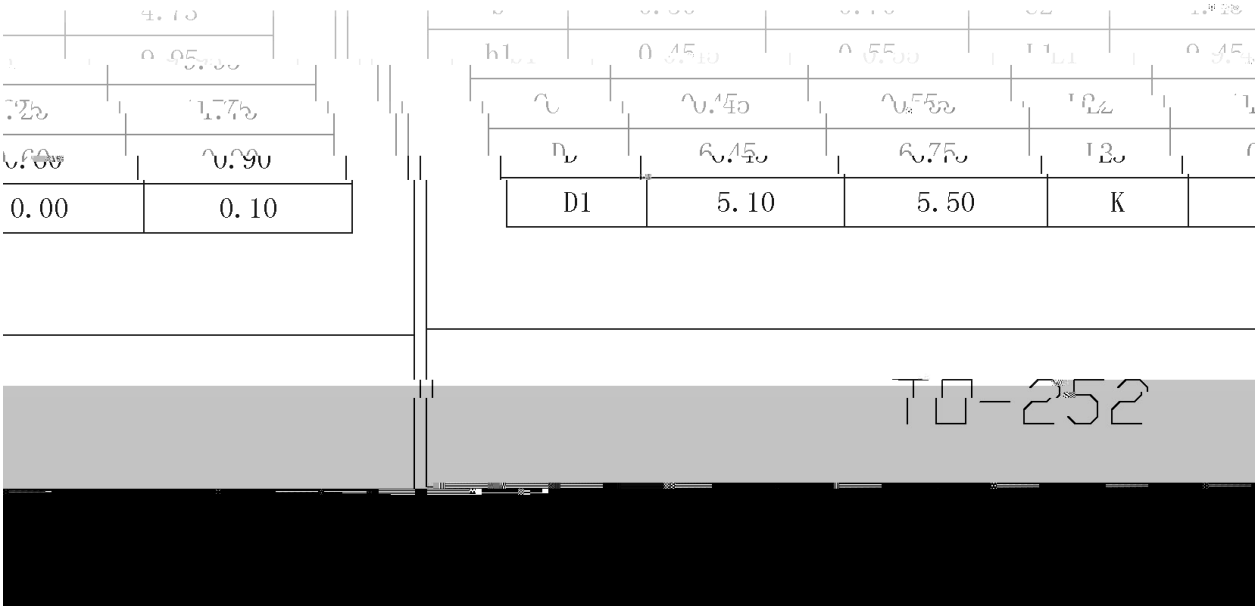
5⁞ Æ ŧ ‖ ˜ ▨╨ : `H ¸ ò lj S Ƈ

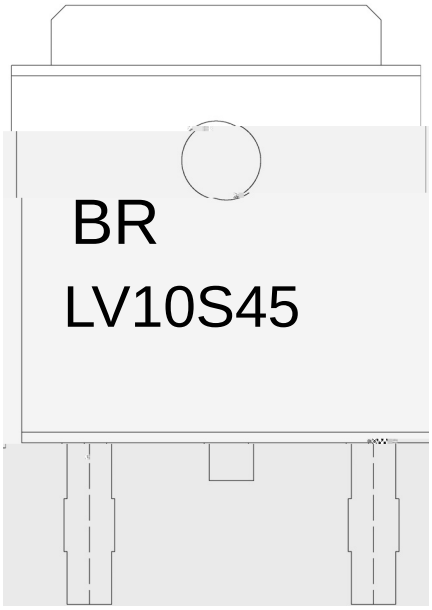

IF - TA
IF(A)
12
10
8
6
4
2
0
25
50
75
100
125
150
175


IFSM
8.3ms Single Half Sine
Wave Jedec Methodl
PEAK FORWARD SURGE CURRENT-(A)
300
275
250
225
200
175
150
125
100
75
50
25
0
0
10
20
30
40
50
60
70
80
90
100
NO.OF CYCLES AT 60HZ



0.00	0.10	D1	5.10	5.50	K





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EU χ	ѭ ϗ и Ґ
0Y43V78 χ	ѭ ϳ ɴ Ґ
---- χ	ѭ ɨ ғ ӈ ɴ Ґ ɪ ҿ ɨ ғ ӈ ɴ Ψ ҏ
Note:	
BR:	Company Code
0Y43V78 χ	Product Type Code.
****:	Lot No. Code, code change with Lot No.